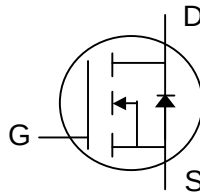


N-CHANNEL ENHANCEMENT-MODE POWER MOSFET

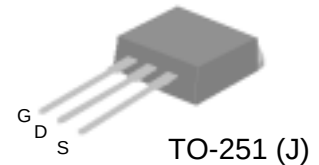
Low gate-charge
Simple drive requirement
Fast switching



BV_{DS} 60V
 $R_{DS(ON)}$ 36mΩ
 I_D 25A

Description

The SSM9971GH is in a TO-252 package, which is widely used for commercial and industrial surface mount applications, and is well suited for low voltage applications such as DC/DC converters. The through-hole version, the SSM9971GJ in TO-251, is available for low-footprint vertical mounting. These devices are manufactured with an advanced process, providing improved on-resistance and switching performance.



 **Pb-free lead finish (second-level interconnect)**

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
$I_D @ T_A=25^{\circ}\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	25	A
$I_D @ T_A=100^{\circ}\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	16	A
I_{DM}	Pulsed Drain Current ¹	80	A
$P_D @ T_A=25^{\circ}\text{C}$	Total Power Dissipation	39	W
	Linear Derating Factor	0.31	W/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Thermal Resistance Junction-case	Max. 3.2	°C/W
Rthj-a	Thermal Resistance Junction-ambient	Max. 110	°C/W

Electrical Characteristics @ $T_J=25^{\circ}\text{C}$ (unless otherwise specified)

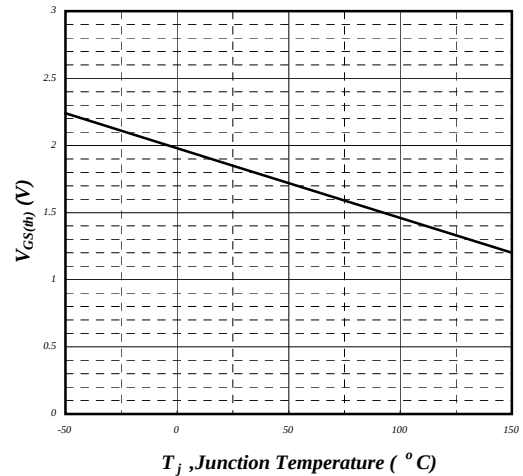
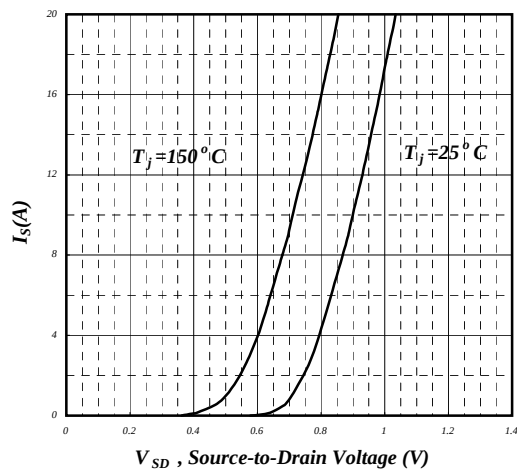
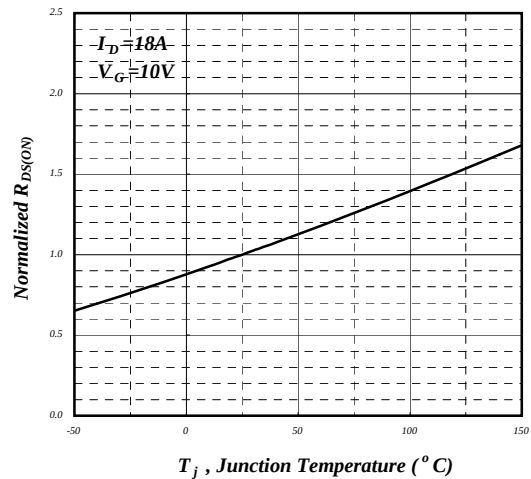
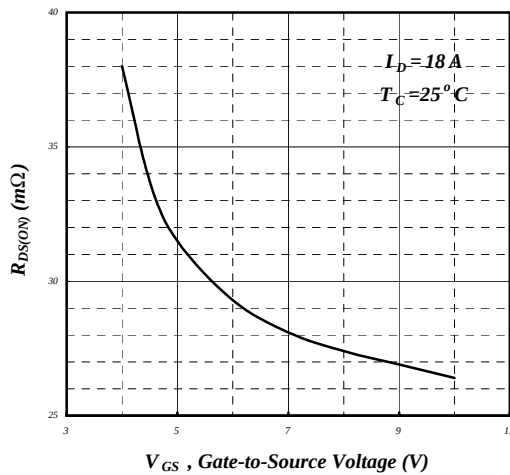
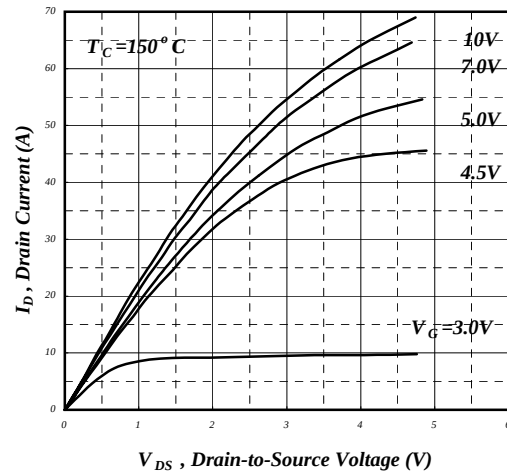
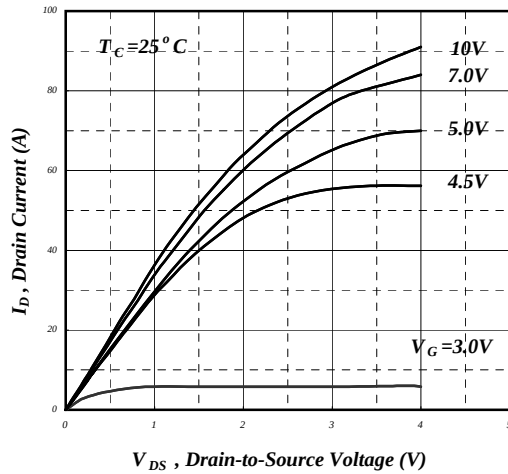
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	-	0.05	-	$\text{V}/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=18A$	-	-	36	$\text{m}\Omega$
		$V_{GS}=4.5V, I_D=12A$	-	-	50	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1	-	3	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=18A$	-	17	-	S
I_{DSS}	Drain-Source Leakage Current ($T_J=25^{\circ}\text{C}$)	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
	Drain-Source Leakage Current ($T_J=150^{\circ}\text{C}$)	$V_{DS}=48V, V_{GS}=0V$	-	-	25	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}= \pm 20V$	-	-	± 100	nA
Q_g	Total Gate Charge ²	$I_D=18A$	-	18	30	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=48V$	-	6	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=4.5V$	-	11	-	nC
$t_{d(on)}$	Turn-on Delay Time ²	$V_{DS}=30V$	-	9	-	ns
t_r	Rise Time	$I_D=18A$	-	24	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{GS}=10V$	-	26	-	ns
t_f	Fall Time	$R_D=1.67\Omega$	-	7	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	1700	2700	pF
C_{oss}	Output Capacitance	$V_{DS}=25V$	-	160	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	110	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_S=25A, V_{GS}=0V$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$I_S=18A, V_{GS}=0V,$ $dI/dt=100A/\mu s$	-	37	-	ns
Q_{rr}	Reverse Recovery Charge		-	38	-	nC

Notes:

1. Pulse width limited by safe operating area.
2. Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.



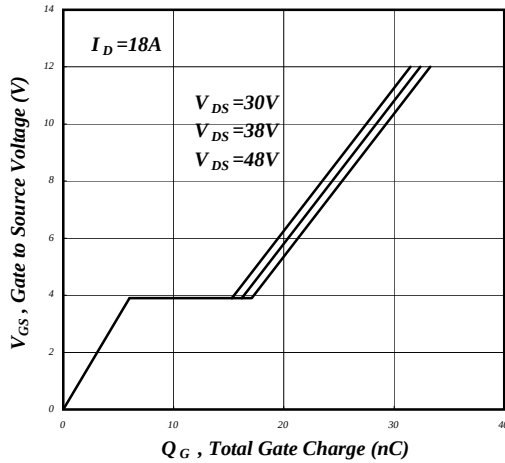


Fig 7. Gate Charge Characteristics

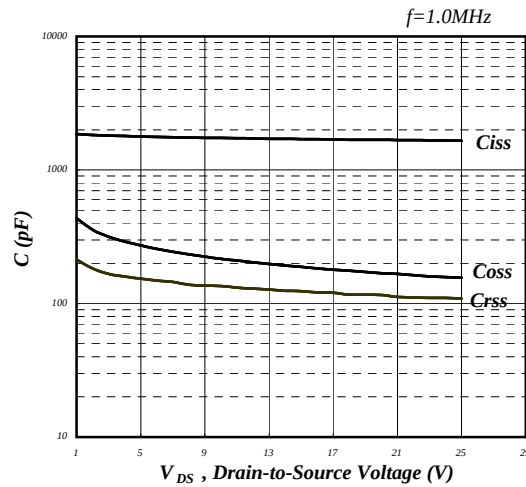


Fig 8. Typical Capacitance Characteristics

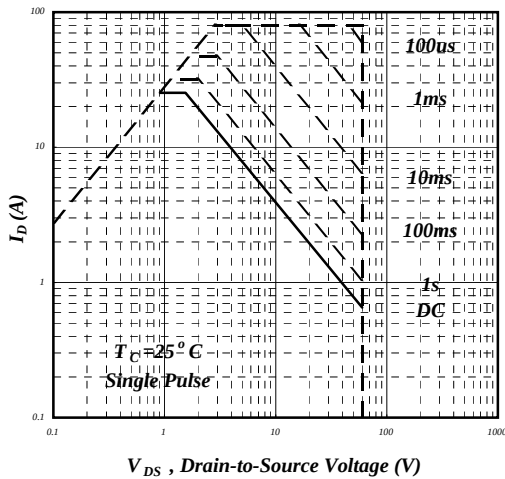


Fig 9. Maximum Safe Operating Area

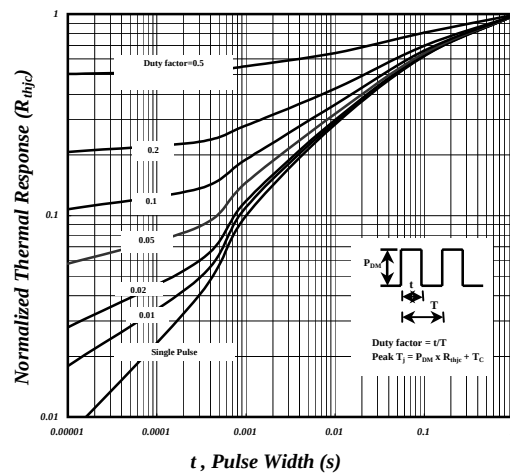


Fig 10. Effective Transient Thermal Impedance

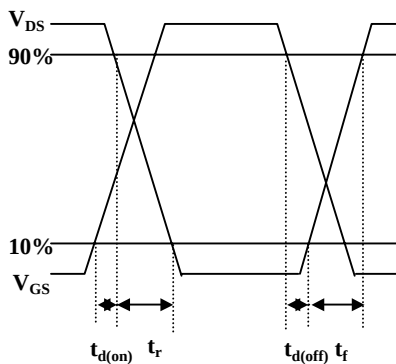


Fig 11. Switching Time Waveform

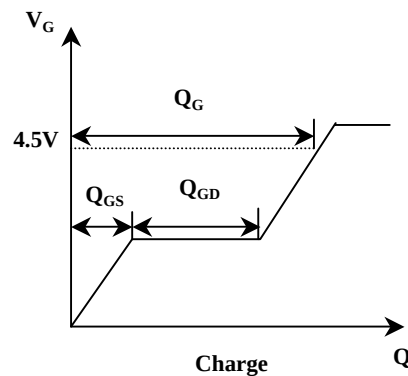


Fig 12. Gate Charge Waveform

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